

# **High Voltage Standard Rectifier**

R	3~ Rectifier				
$V_{RRM}$	=	2200 V	1		
$I_{DAV}$	=	90 A			
$I_{FSM}$	=	370 A			

Half 3~ Bridge, Common Anode

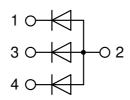
Part number

#### DNA90YA2200NA



Backside: isolated





#### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

## **Applications:**

- Diode for main rectification
- For single and three phase bridge configurations

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
  Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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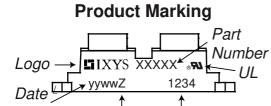


Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			2300	V
V <sub>RRM</sub>	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			2200	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 2200 V	$T_{VJ} = 25^{\circ}C$			100	μΑ
		$V_R = 2200 V$	$T_{VJ} = 150$ °C			1.5	mΑ
V <sub>F</sub>	forward voltage drop	I <sub>F</sub> = 30 A	$T_{VJ} = 25^{\circ}C$			1.23	V
		$I_F = 90 A$				1.70	٧
		I <sub>F</sub> = 30 A	T <sub>VJ</sub> = 125°C			1.21	٧
		$I_F = 90 A$				1.85	٧
IDAV	bridge output current	T <sub>c</sub> = 85°C	T <sub>vJ</sub> = 150°C			90	Α
		rectangular d = ⅓					
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 150°C			0.86	V
r <sub>F</sub>	slope resistance \( \) for power	loss calculation only				11.4	mΩ
R <sub>thJC</sub>	thermal resistance junction to ca	ase				1.2	K/W
R <sub>thCH</sub>	thermal resistance case to heats	sink			0.1		K/W
P <sub>tot</sub>	total power dissipation		$T_{C} = 25^{\circ}C$			100	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			370	Α
		t = 8,3  ms; (60 Hz), sine	$V_R = 0 V$			400	Α
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			315	Α
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			340	Α
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			685	A <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			665	A²s
		t = 10 ms; (50 Hz), sine	T <sub>vJ</sub> = 150°C			495	A <sup>2</sup> s
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			480	A²s
C <sub>J</sub>	junction capacitance	$V_{B} = 700 \text{ V}; f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		7		pF



# **DNA90YA2200NA**

Package	Package SOT-227B (minibloc)				ı	Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit	
I <sub>RMS</sub>	RMS current	per terminal					150	Α	
T <sub>VJ</sub>	virtual junction temperatur	re			-40		150	°C	
T <sub>op</sub>	operation temperature				-40		125	°C	
T <sub>stg</sub>	storage temperature				-40		150	°C	
Weight						30		g	
M <sub>D</sub>	mounting torque				1.1		1.5	Nm	
$\mathbf{M}_{T}$	terminal torque				1.1		1.5	Nm	
d <sub>Spp/App</sub>	oroonogo diatanoo on our	face Latriking diatance through air	terminal to terminal	10.5	3.2			mm	
d <sub>Spb/Apb</sub>	creepage distance on sun	face   striking distance through air	terminal to backside	8.6	6.8			mm	
V <sub>ISOL</sub>	isolation voltage	t = 1 second	50/00 LL 51/10 L		3000			٧	
		t = 1 minute	50/60 Hz, RMS; IISOL ≤ 1 mA		2500			٧	



Lot#

Location

#### Part description

D = Diode N = High Voltage Standard Rectifier

A = (>= 2000V)

90 = Current Rating [A]

YA = Half 3~ Bridge, Common Anode

2200 = Reverse Voltage [V]

NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DNA90YA2200NA	DNA90YA2200NA	Tube	10	513730

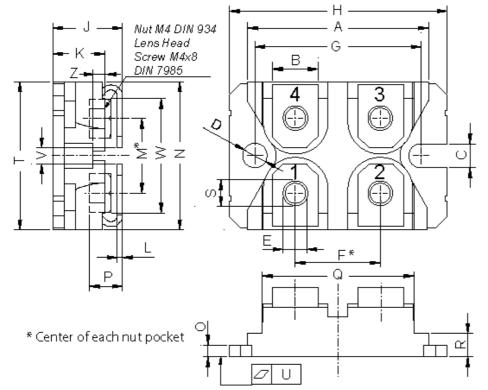
Similar Part	Package	Voltage class
DNA90YC2200NA	SOT-227B (minibloc)	2200

Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 150^{\circ}C$
$I \rightarrow V_0$	)—[R <sub>0</sub> ]-	Rectifier		
V <sub>0 max</sub>	threshold voltage	0.86		V
R <sub>0 max</sub>	slope resistance *	9.5		mΩ





## Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
DIIII.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	

